Document Title

256K x 16 Hight Speed SRAM with 3.3V

Revision History

Revision No	History	Draft Date	Remark
0A	Initial Draft	September 11,2001	

The attached datasheets are provided by ICSI. Integrated Circuit Solution Inc reserve the right to change the specifications and products. ICSI will answer to your questions about device. If you have any questions, please contact the ICSI offices.

256K x 16 HIGH SPEED ASYNCHRONOUS CMOS STATIC RAM WITH 3.3V SUPPLY

FEATURES

- High-speed access time: 8, 10, 12, and 15 ns
- CMOS low power operation
- TTL compatible interface levels
- Single 3.3V ± 10% power supply
- Fully static operation: no clock or refresh required
- Three state outputs
- Data control for upper and lower bytes
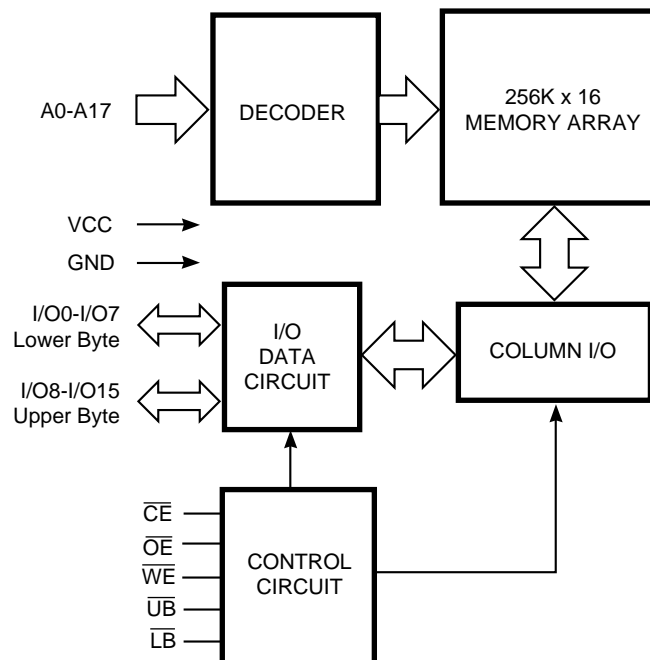- Industrial temperature available

DESCRIPTION

The *ICSI* IC61LV25616 is a high-speed, 4,194,304-bit static RAM organized as 262,144 words by 16 bits. It is fabricated using *ICSI*'s high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields high-performance and low power consumption devices.

When $\overline{CE}$ is HIGH (deselected), the device assumes a standby mode at which the power dissipation can be reduced down with CMOS input levels.

Easy memory expansion is provided by using Chip Enable and Output Enable inputs, $\overline{CE}$ and $\overline{OE}$. The active LOW Write Enable ($\overline{WE}$) controls both writing and reading of the memory. A data byte allows Upper Byte ($\overline{UB}$) and Lower Byte ($\overline{LB}$) access.

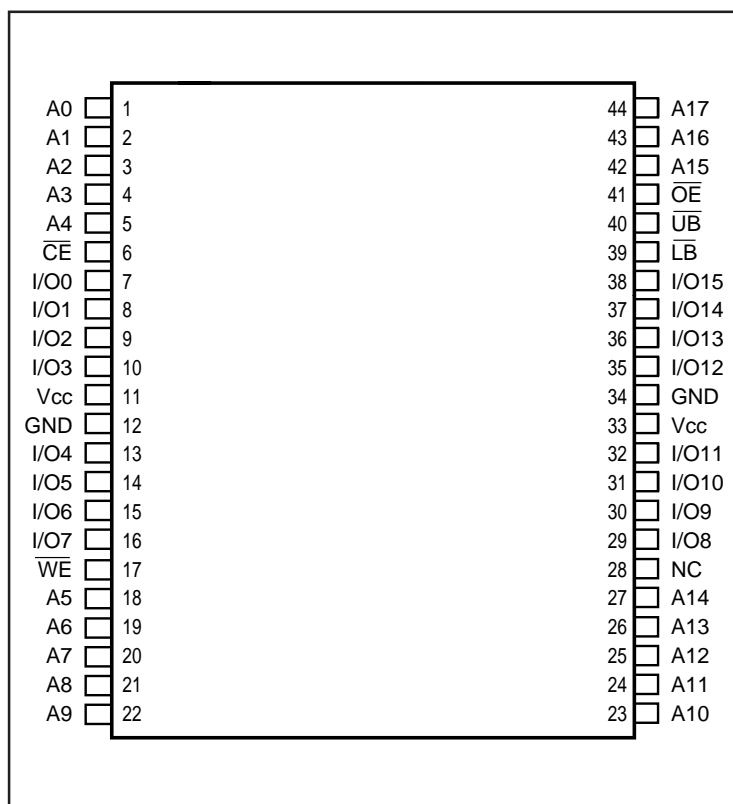The IC61LV25616 is packaged in the JEDEC standard 44-pin 400mil SOJ, 44 pin 400mil TSOP-2 and 48-pin 6*8 TF-BGA.
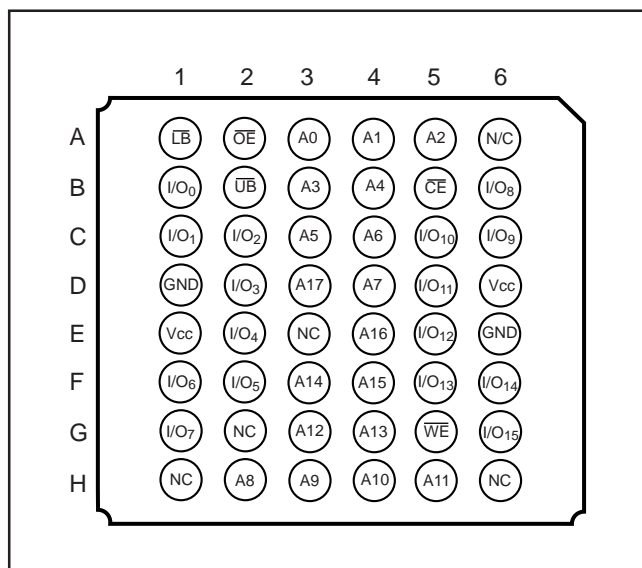
FUNCTIONAL BLOCK DIAGRAM

PIN CONFIGURATIONS

44-Pin TSOP-2 and SOJ

Pin	Signal		Pin	Signal
1	A0		44	A17
2	A1		43	A16
3	A2		42	A15
4	A3		41	$\overline{OE}$
5	A4		40	$\overline{UB}$
6	$\overline{CE}$		39	$\overline{LB}$
7	I/O0		38	I/O15
8	I/O1		37	I/O14
9	I/O2		36	I/O13
10	I/O3		35	I/O12
11	Vcc		34	GND
12	GND		33	Vcc
13	I/O4		32	I/O11
14	I/O5		31	I/O10
15	I/O6		30	I/O9
16	I/O7		29	I/O8
17	$\overline{WE}$		28	NC
18	A5		27	A14
19	A6		26	A13
20	A7		25	A12
21	A8		24	A11
22	A9		23	A10

48-Pin TF-BGA

	1	2	3	4	5	6
A	$\overline{LB}$	$\overline{OE}$	A0	A1	A2	N/C
B	I/O0	$\overline{UB}$	A3	A4	$\overline{CE}$	I/O8
C	I/O1	I/O2	A5	A6	I/O10	I/O9
D	GND	I/O3	A17	A7	I/O11	Vcc
E	Vcc	I/O4	NC	A16	I/O12	GND
F	I/O6	I/O5	A14	A15	I/O13	I/O14
G	I/O7	NC	A12	A13	$\overline{WE}$	I/O15
H	NC	A8	A9	A10	A11	NC

PIN DESCRIPTIONS

A0-A17	Address Inputs
I/O0-I/O15	Data Inputs/Outputs
$\overline{CE}$	Chip Enable Input
$\overline{OE}$	Output Enable Input
$\overline{WE}$	Write Enable Input

$\overline{LB}$	Lower-byte Control (I/O0-I/O7)
$\overline{UB}$	Upper-byte Control (I/O8-I/O15)
NC	No Connection
Vcc	Power
GND	Ground

TRUTH TABLE

Mode	$\overline{WE}$	$\overline{CE}$	$\overline{OE}$	$\overline{LB}$	$\overline{UB}$	I/O PIN I/O0-I/O7	I/O8-I/O15	Vcc Current
Not Selected	X	H	X	X	X	High-Z	High-Z	I_{SB1}, I_{SB2}
Output Disabled	H	L	H	X	X	High-Z	High-Z	I_{CC}
	X	L	X	H	H	High-Z	High-Z	
Read	H	L	L	L	H	D_{OUT}	High-Z	I_{CC}
	H	L	L	H	L	High-Z	D_{OUT}	
	H	L	L	L	L	D_{OUT}	D_{OUT}	
Write	L	L	X	L	H	D_{IN}	High-Z	I_{CC}
	L	L	X	H	L	High-Z	D_{IN}	
	L	L	X	L	L	D_{IN}	D_{IN}	

ABSOLUTE MAXIMUM RATINGS[1]

Symbol	Parameter	Value	Unit
V_{TERM}	Terminal Voltage with Respect to GND	−0.5 to Vcc+0.5	V
T_{BIAS}	Temperature Under Bias	−45 to +90	°C
V_{CC}	Vcc Related to GND	−0.3 to +4.0	V
T_{STG}	Storage Temperature	−65 to +150	°C
P_T	Power Dissipation	1.0	W

Note:
1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

OPERATING RANGE

Range	Ambient Temperature	Vcc
Commercial	0°C to +70°C	3.3V ± 10%
Industrial	−40°C to +85°C	3.3V ± 10%

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions		Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	Vcc = Min., IoH = −4.0 mA		2.4	—	V
V_{OL}	Output LOW Voltage	Vcc = Min., IoL = 8.0 mA		—	0.4	V
V_{IH}	Input HIGH Voltage			2.0	Vcc + 0.3	V
V_{IL}	Input LOW Voltage[1]			−0.3	0.8	V
I_{LI}	Input Leakage	GND ≤ VIN ≤ Vcc	Com.	−1	1	µA
			Ind.	−5	5	
I_{LO}	Output Leakage	GND ≤ VOUT ≤ Vcc Outputs Disabled	Com.	−1	1	µA
			Ind.	−5	5	

Notes:
1. VIL (min.) = −2.0V for pulse width less than 10 ns.
2. The Vcc operating range for 8 ns is 3.3V +10%, -5%.

POWER SUPPLY CHARACTERISTICS[1] (Over Operating Range)

Symbol	Parameter	Test Conditions		-8 ns Min.	-8 ns Max.	-10 ns Min.	-10 ns Max.	-12 ns Min.	-12 ns Max.	-15 ns Min.	-15 ns Max.	Unit
I_{CC}	Vcc Dynamic Operating Supply Current	Vcc = Max., IOUT = 0 mA, f = fMAX	Com.	—	350	—	320	—	290	—	260	mA
			Ind.	—	360	—	330	—	300	—	270	
I_{SB1}	TTL Standby Current (TTL Inputs)	Vcc = Max., VIN = VIH or VIL $\overline{CE}$ ≥ VIH, f = 0	Com.	—	55	—	55	—	55	—	55	mA
			Ind.	—	65	—	65	—	65	—	65	
I_{SB2}	CMOS Standby Current (CMOS Inputs)	Vcc = Max., $\overline{CE}$ ≥ Vcc − 0.2V, VIN ≥ Vcc − 0.2V, or VIN ≤ 0.2V, f = 0	Com.	—	10	—	10	—	10	—	10	mA
			Ind.	—	15	—	15	—	15	—	15	

Note:
1. At f = fMAX, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.

Integrated Circuit Solution Inc.

AHSR022-0A 09/11/2001

CAPACITANCE[1]

Symbol	Parameter	Conditions	Max.	Unit
C_{IN}	Input Capacitance	$V_{IN} = 0V$	6	pF
C_{OUT}	Input/Output Capacitance	$V_{OUT} = 0V$	8	pF

Note:
1. Tested initially and after any design or process changes that may affect these parameters.

READ CYCLE SWITCHING CHARACTERISTICS[1] (Over Operating Range)

Symbol	Parameter	-8 Min.	-8 Max.	-10 Min.	-10 Max.	-12 Min.	-12 Max.	-15 Min.	-15 Max.	Unit
t_{RC}	Read Cycle Time	8	—	10	—	12	—	15	—	ns
t_{AA}	Address Access Time	—	8	—	10	—	12	—	15	ns
t_{OHA}	Output Hold Time	3	—	3	—	3	—	3	—	ns
t_{ACE}	$\overline{CE}$ Access Time	—	8	—	10	—	12	—	15	ns
t_{DOE}	$\overline{OE}$ Access Time	—	4	—	5	—	6	—	7	ns
t_{HZOE}[2]	$\overline{OE}$ to High-Z Output	0	4	—	5	—	6	0	6	ns
t_{LZOE}[2]	$\overline{OE}$ to Low-Z Output	0	—	0	—	0	—	0	—	ns
t_{HZCE}[2]	$\overline{CE}$ to High-Z Output	0	4	0	5	0	6	0	6	ns
t_{LZCE}[2]	$\overline{CE}$ to Low-Z Output	3	—	3	—	3	—	3	—	ns
t_{BA}	$\overline{LB}$, $\overline{UB}$ Access Time	—	4	—	5	—	6	—	7	ns
t_{HZB}	$\overline{LB}$, $\overline{UB}$ to High-Z Output	0	4	0	5	0	6	0	6	ns
t_{LZB}	$\overline{LB}$, $\overline{UB}$ to Low-Z Output	0	—	0	—	0	—	0	—	ns

Notes:
1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1a.
2. Tested with the load in Figure 1b. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.
3. Not 100% tested.

AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	3 ns
Input and Output Timing and Reference Level	1.5V
Output Load	See Figures 1 and 2

Notes:
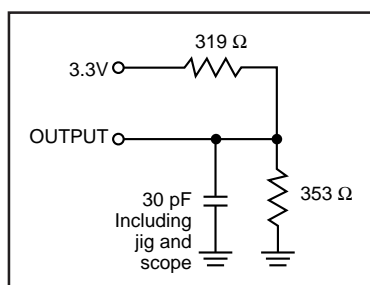1. The Vcc operating range for 8 ns is 3.3V +10%, -5%.
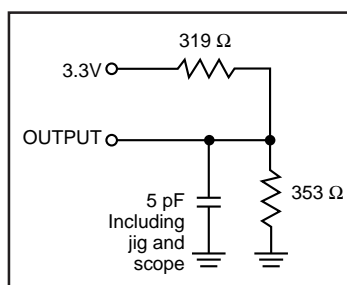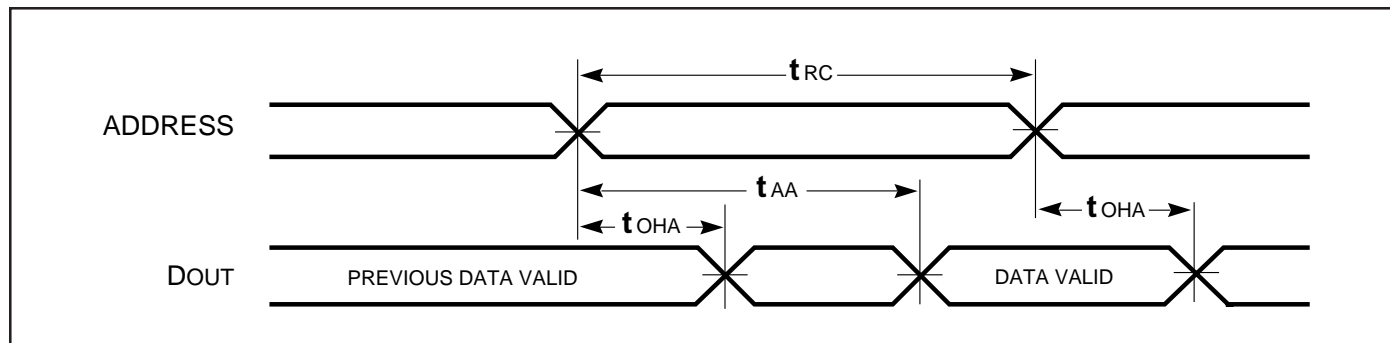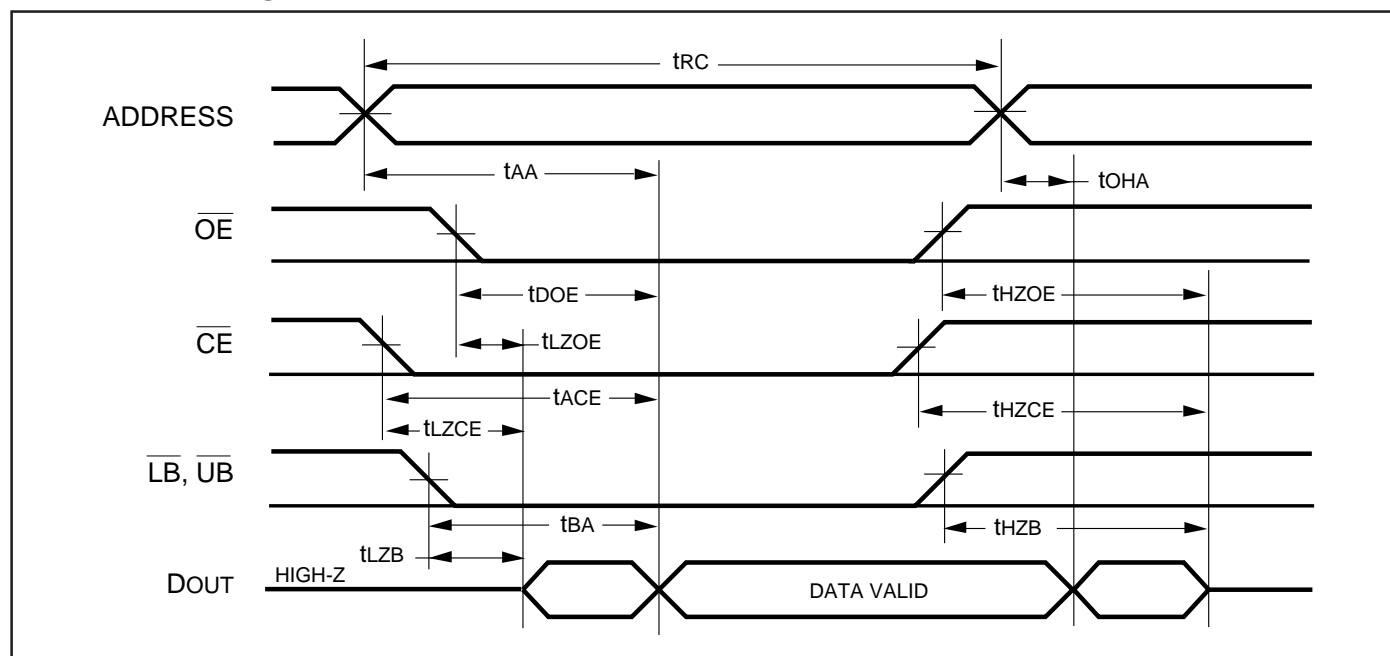
AC TEST LOADS

Figure 1

Figure 2

AC WAVEFORMS

READ CYCLE NO. 1[1,2] (Address Controlled) ($\overline{CE} = \overline{OE} = V_{IL}$, $\overline{UB}$ or $\overline{LB} = V_{IL}$)

READ CYCLE NO. 2[1,3]

Notes:
1. $\overline{WE}$ is HIGH for a Read Cycle.
2. The device is continuously selected. $\overline{OE}$, $\overline{CE}$, $\overline{UB}$, or $\overline{LB} = V_{IL}$.
3. Address is valid prior to or coincident with $\overline{CE}$ LOW transition.

Integrated Circuit Solution Inc.
AHSR022-0A 09/11/2001

WRITE CYCLE SWITCHING CHARACTERISTICS[1,3] (Over Operating Range)

Symbol	Parameter	-8 Min.	-8 Max.	-10 Min.	-10 Max.	-12 Min.	-12 Max.	-15 Min.	-15 Max.	Unit
t_{WC}	Write Cycle Time	8	—	10	—	12	—	15	—	ns
t_{SCE}	$\overline{CE}$ to Write End	7	—	8	—	9	—	10	—	ns
t_{AW}	Address Setup Time to Write End	7	—	8	—	9	—	10	—	ns
t_{HA}	Address Hold from Write End	0	—	0	—	0	—	0	—	ns
t_{SA}	Address Setup Time	0	—	0	—	0	—	0	—	ns
t_{PWB}	$\overline{LB}$, $\overline{UB}$ Valid to End of Write	7	—	8	—	9	—	10	—	ns
t_{PWE}	$\overline{WE}$ Pulse Width	7	—	8	—	9	—	10	—	ns
t_{SD}	Data Setup to Write End	4.5	—	5	—	6	—	7	—	ns
t_{HD}	Data Hold from Write End	0	—	0	—	0	—	0	—	ns
t_{HZWE}[2]	$\overline{WE}$ LOW to High-Z Output	—	4	—	5	—	6	—	7	ns
t_{LZWE}[2]	$\overline{WE}$ HIGH to Low-Z Output	3	—	3	—	3	—	3	—	ns

Notes:
1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1a.
2. Tested with the load in Figure 1b. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.
3. The internal write time is defined by the overlap of $\overline{CE}$ LOW and $\overline{UB}$ or $\overline{LB}$, and $\overline{WE}$ LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
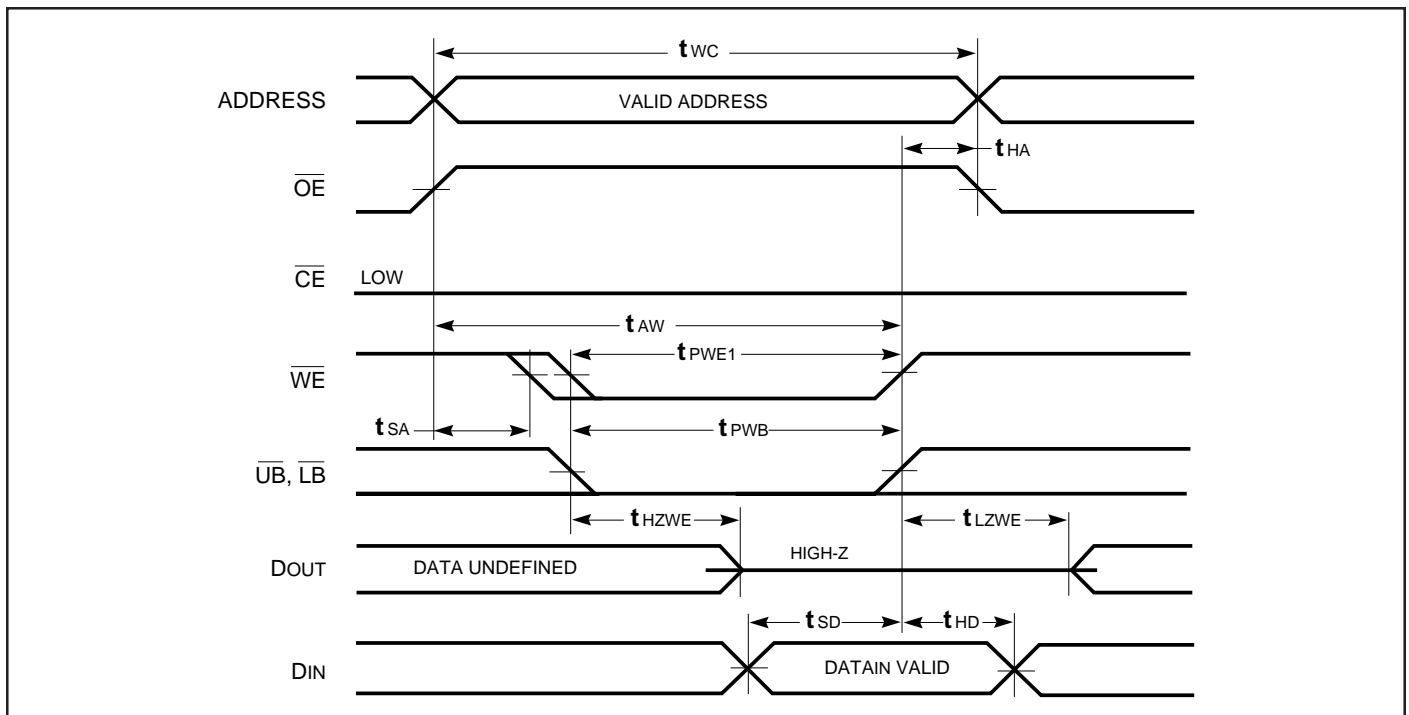
AC WAVEFORMS
WRITE CYCLE NO. 1 ($\overline{\text{CE}}$ Controlled, $\overline{\text{OE}}$ is HIGH or LOW) [1]
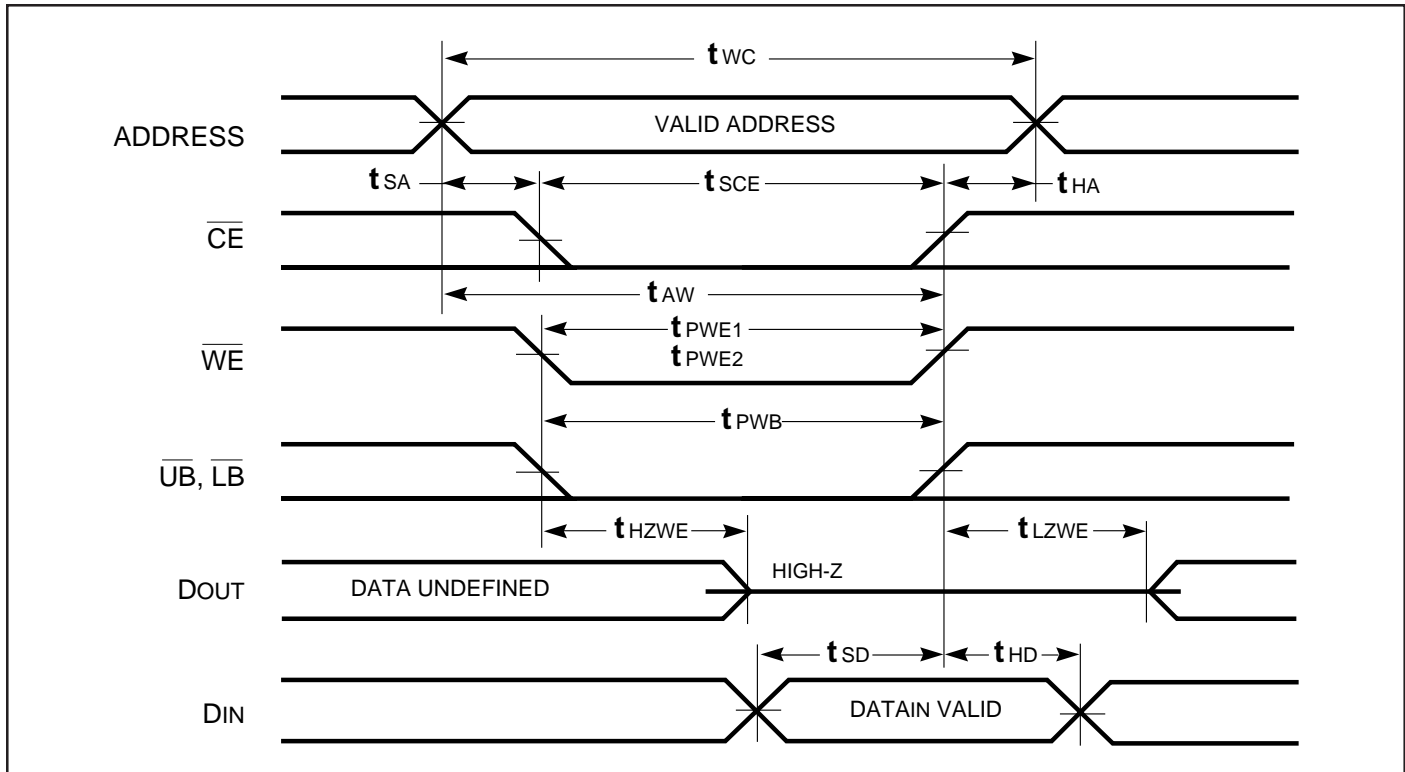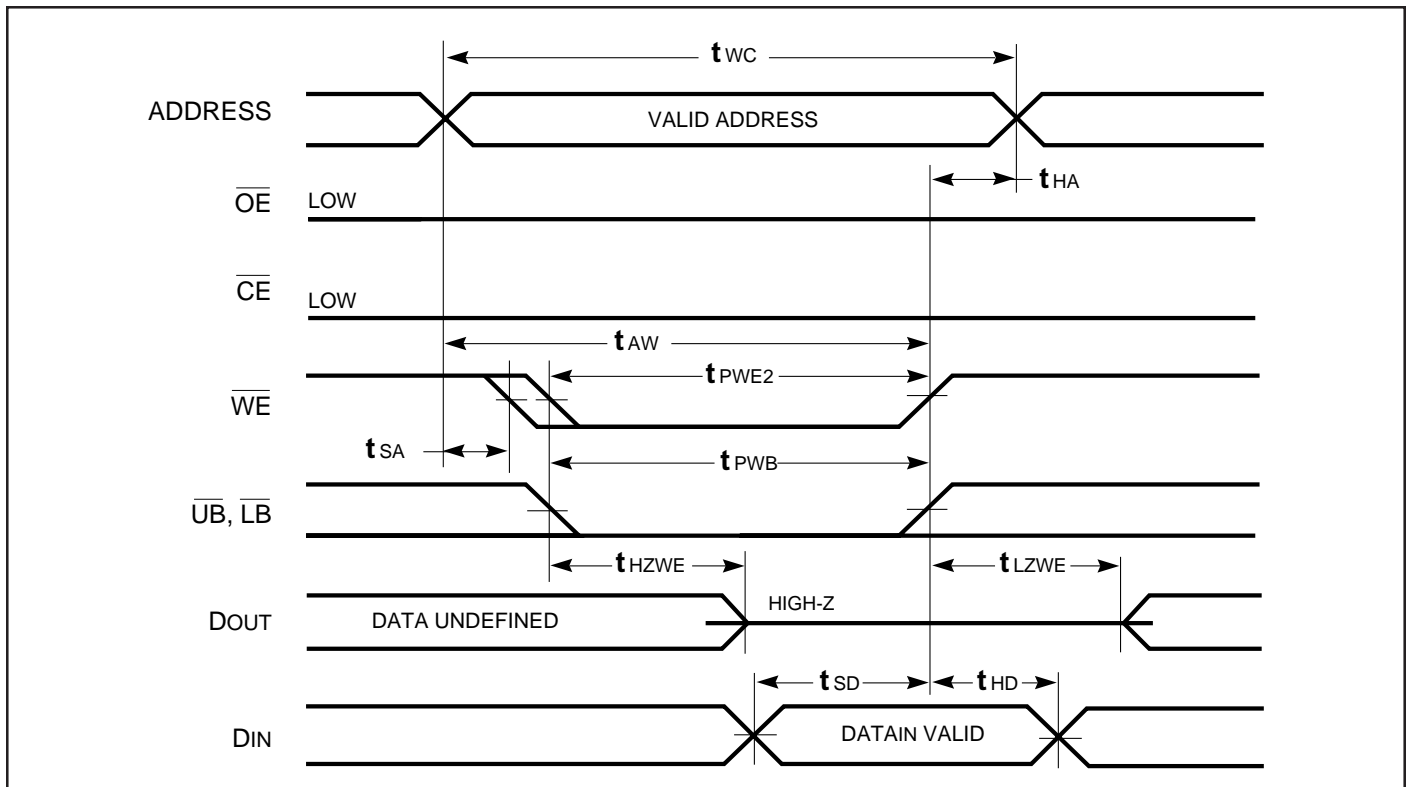

Notes:

1. WRITE is an internally generated signal asserted during an overlap of the LOW states on the $\overline{\text{CE}}$ and $\overline{\text{WE}}$ inputs and at least one of the $\overline{\text{LB}}$ and $\overline{\text{UB}}$ inputs being in the LOW state.

2. WRITE = $(\overline{\text{CE}})$ [$(\overline{\text{LB}})$ = $(\overline{\text{UB}})$] $(\overline{\text{WE}})$.

AC WAVEFORMS

WRITE CYCLE NO. 2 ($\overline{WE}$ Controlled. $\overline{OE}$ is HIGH During Write Cycle) [1,2]

WRITE CYCLE NO. 3 ($\overline{WE}$ Controlled. $\overline{OE}$ is LOW During Write Cycle) [1]

AC WAVEFORMS

WRITE CYCLE NO. 4 ($\overline{\text{LB}}$, $\overline{\text{UB}}$ Controlled, Back-to-Back Write) [1,3]
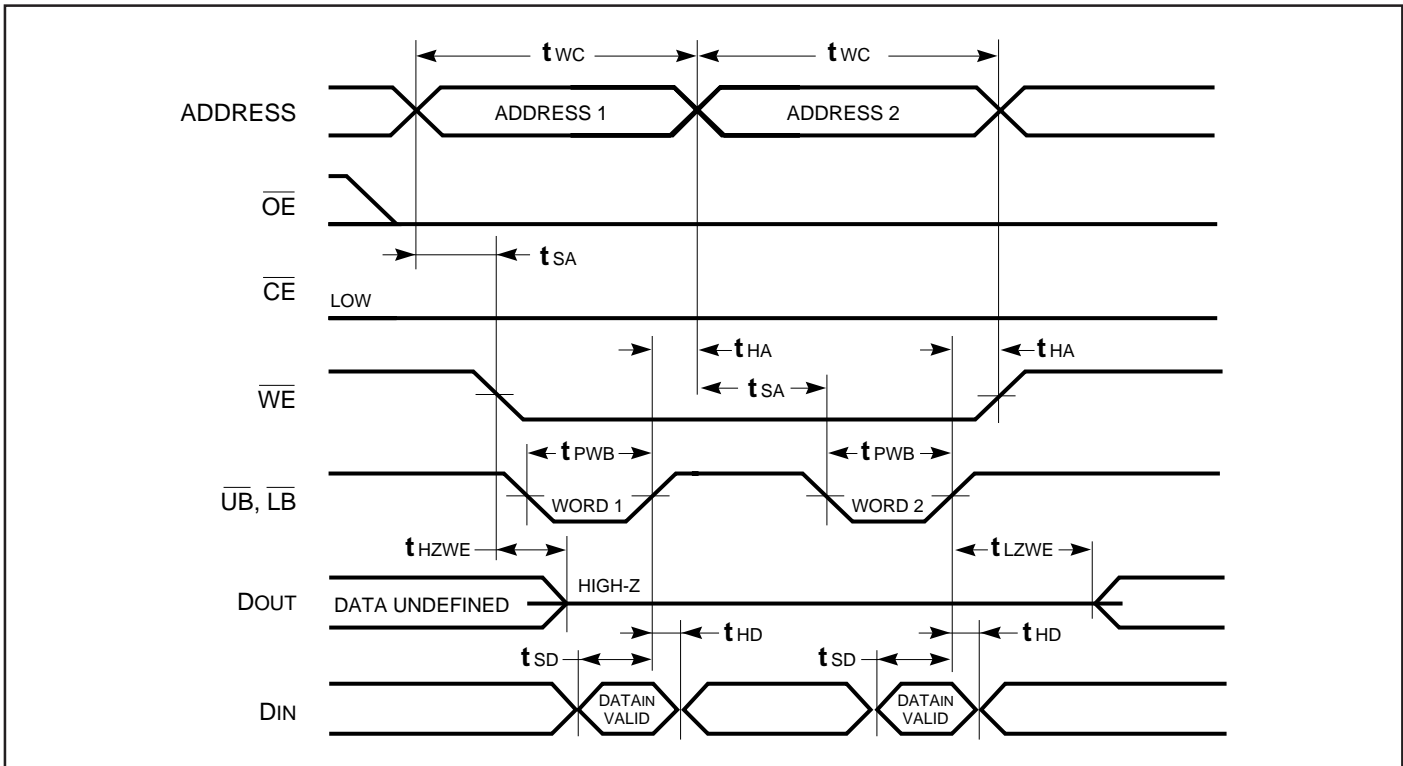
Notes:
1. The internal Write time is defined by the overlap of $\overline{\text{CE}}$ = LOW, $\overline{\text{UB}}$ and/or $\overline{\text{LB}}$ = LOW, and $\overline{\text{WE}}$ = LOW. All signals must be in valid states to initiate a Write, but any can be deasserted to terminate the Write. The t_{SA}, t_{HA}, t_{SD}, and t_{HD} timing is referenced to the rising or falling edge of the signal that terminates the Write.
2. Tested with $\overline{\text{OE}}$ HIGH for a minimum of 4 ns before $\overline{\text{WE}}$ = LOW to place the I/O in a HIGH-Z state.
3. $\overline{\text{WE}}$ may be held LOW across many address cycles and the $\overline{\text{LB}}$, $\overline{\text{UB}}$ pins can be used to control the Write function.

ORDERING INFORMATION
Commercial Range: 0°C to +70°C

Speed (ns)	Order Part No.	Package
8	IC61LV25616-8T	400mil TSOP-2
	IC61LV25616-8K	400mil SOJ
	IC61LV25616-8B	6*8mm TF-BGA
10	IC61LV25616-10T	400mil TSOP-2
	IC61LV25616-10K	400mil SOJ
	IC61LV25616-10B	6*8mm TF-BGA
12	IC61LV25616-12T	400mil TSOP-2
	IC61LV25616-12K	400mil SOJ
	IC61LV25616-12B	6*8mm TF-BGA
15	IC61LV25616-15T	400mil TSOP-2
	IC61LV25616-15K	400mil SOJ
	IC61LV25616-15B	6*8mm TF-BGA

ORDERING INFORMATION
Industrial Range: –40°C to +85°C

Speed (ns)	Order Part No.	Package
8	IC61LV25616-8TI	400mil TSOP-2
	IC61LV25616-8KI	400mil SOJ
	IC61LV25616-8BI	6*8mm TF-BGA
10	IC61LV25616-10TI	400mil TSOP-2
	IC61LV25616-10KI	400mil SOJ
	IC61LV25616-10BI	6*8mm TF-BGA
12	IC61LV25616-12TI	400mil TSOP-2
	IC61LV25616-12KI	400mil SOJ
	IC61LV25616-12BI	6*8mm TF-BGA
15	IC61LV25616-15TI	400mil TSOP-2
	IC61LV25616-15KI	400mil SOJ
	IC61LV25616-15BI	6*8mm TF-BGA